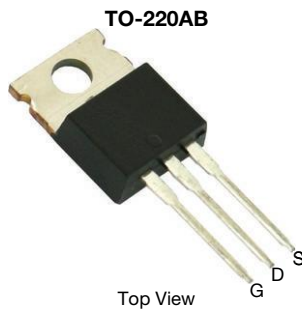


IXTP86N20T-VB Datasheet

N-Channel 200 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (TYP.)
200	0.017 at V _{GS} = 10 V	80	64 nC
	0.018 at V _{GS} = 7.5 V	78	



FEATURES

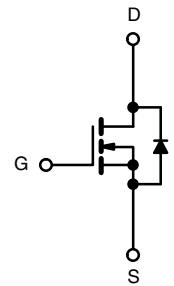
- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	200	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	80
		T _C = 70 °C	65
Pulsed Drain Current (t = 100 μs)	I _{DM}	240	A
Avalanche Current	I _{AS}	60	
Single Avalanche Energy ^a	E _{AS}	180	mJ
Maximum Power Dissipation ^a	P _D	T _C = 25 °C	375 ^b
		T _C = 125 °C	125 ^b
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W
Junction-to-Case (Drain)	R _{thJC}	0.4	

Notes

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	200	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	-	4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	150	
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	5	mA
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	90	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$	-	0.017	-	Ω
		$V_{GS} = 7.5\text{ V}, I_D = 30\text{ A}$	-	0.018	-	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	-	75	-	S
Dynamic ^b						
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	4132	-	pF
Output Capacitance	C_{OSS}		-	246	-	
Reverse Transfer Capacitance	C_{RSS}		-	21	-	
Total Gate Charge ^c	Q_g	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 60\text{ A}$	-	64	96	nC
Gate-Source Charge ^c	Q_{gs}		-	16.7	-	
Gate-Drain Charge ^c	Q_{gd}		-	16.9	-	
Gate Resistance	R_g	$f = 1\text{ MHz}$	1.5	3	5	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 1.66\text{ }\Omega$ $I_D \cong 60\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	13	26	ns
Rise Time ^c	t_r		-	112	200	
Turn-Off Delay Time ^c	$t_{d(off)}$		-	35	70	
Fall Time ^c	t_f		-	80	150	
Drain-Source Body Diode Ratings and Characteristics ^b ($T_C = 25\text{ }^\circ\text{C}$)						
Pulsed Current ($t = 100\text{ }\mu\text{s}$)	I_{SM}		-	-	240	A
Forward Voltage ^a	V_{SD}	$I_F = 10\text{ A}, V_{GS} = 0\text{ V}$	-	0.8	1.2	V
Reverse Recovery Time	t_{rr}	$I_F = 30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	160	320	ns
Peak Reverse Recovery Charge	$I_{RM(REC)}$		-	11	20	A
Reverse Recovery Charge	Q_{rr}		-	0.9	1.8	μC

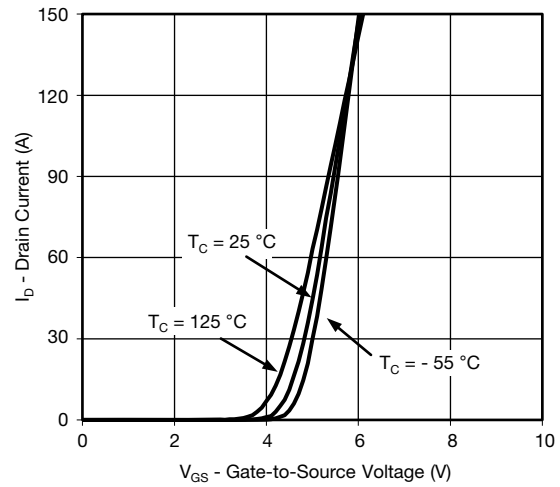
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

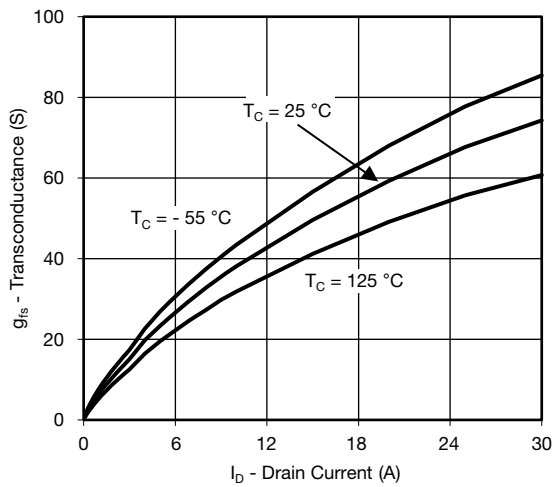
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



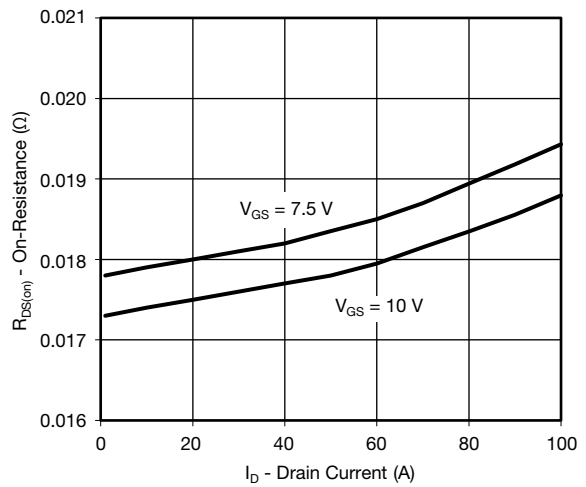
Output Characteristics



Transfer Characteristics



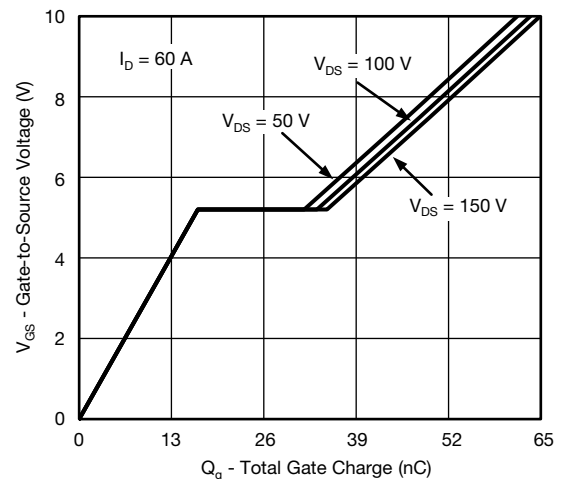
Transconductance



On-Resistance vs. Drain Current



Capacitance

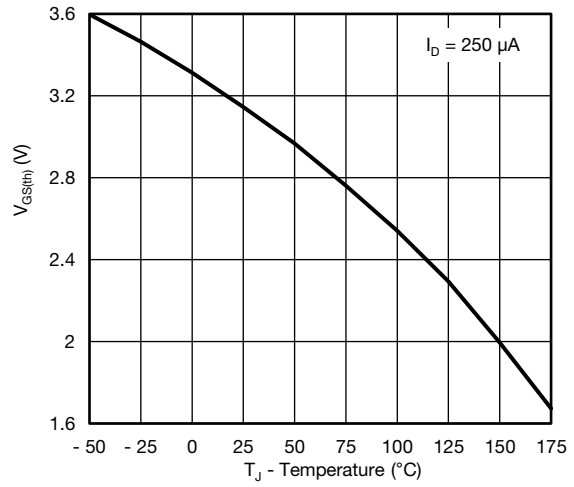


Gate Charge

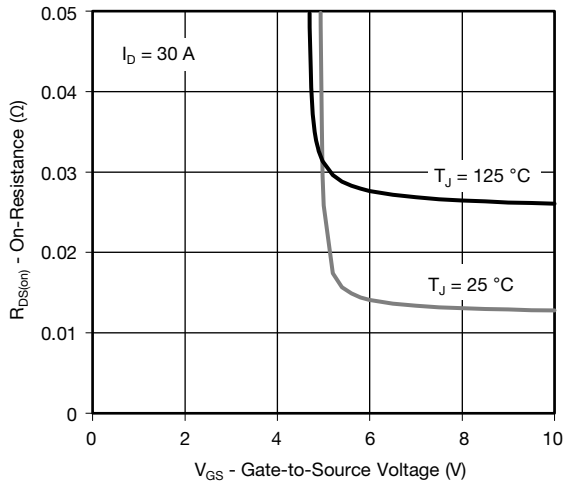
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



On-Resistance vs. Junction Temperature



Threshold Voltage



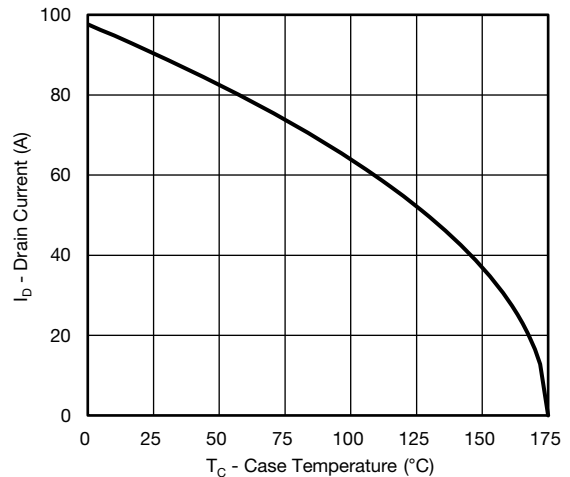
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



Current De-rating

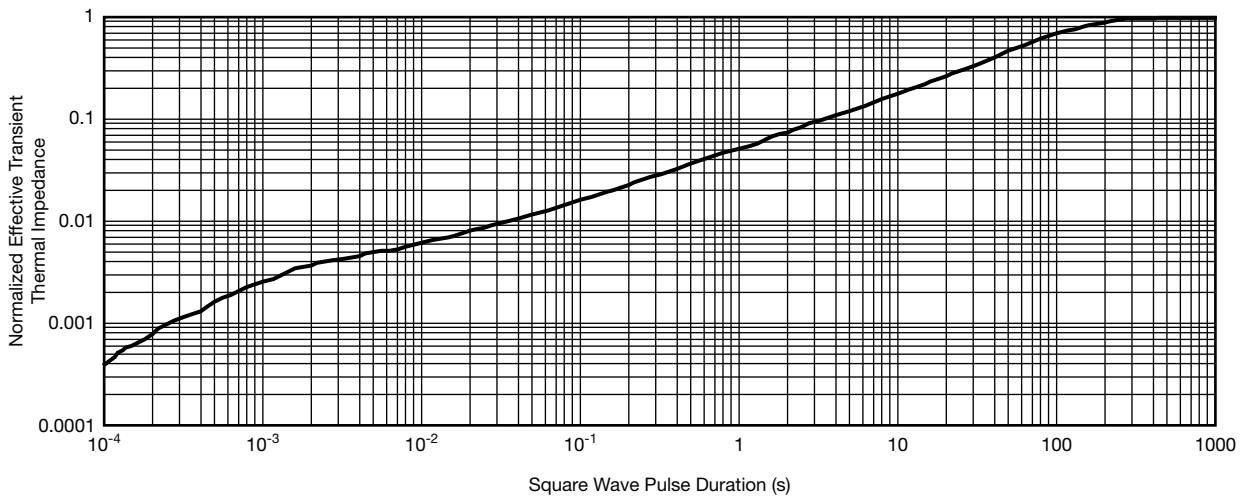
THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



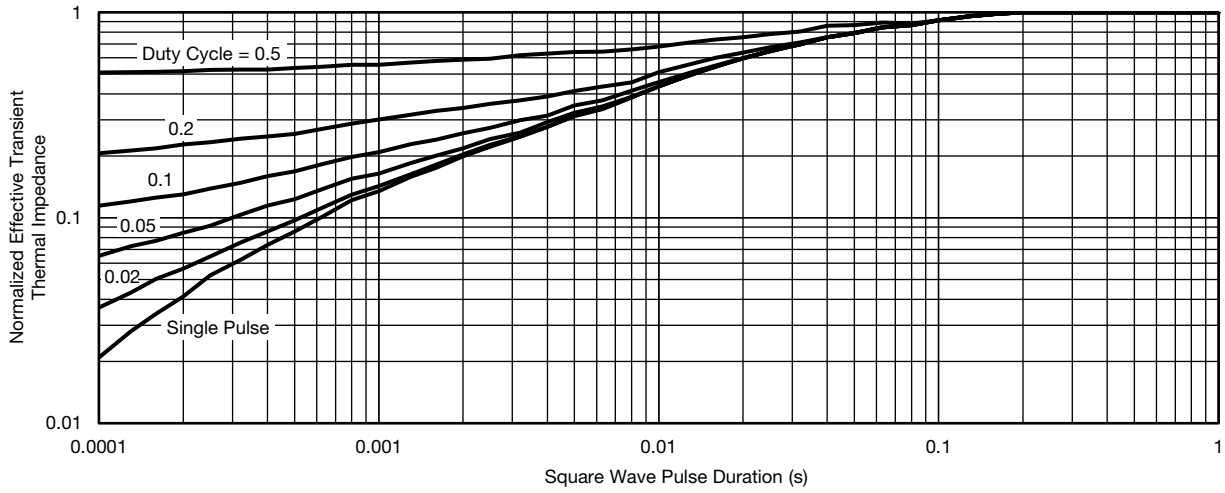
Safe Operating Area



Single Pulse Avalanche Current Capability vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient

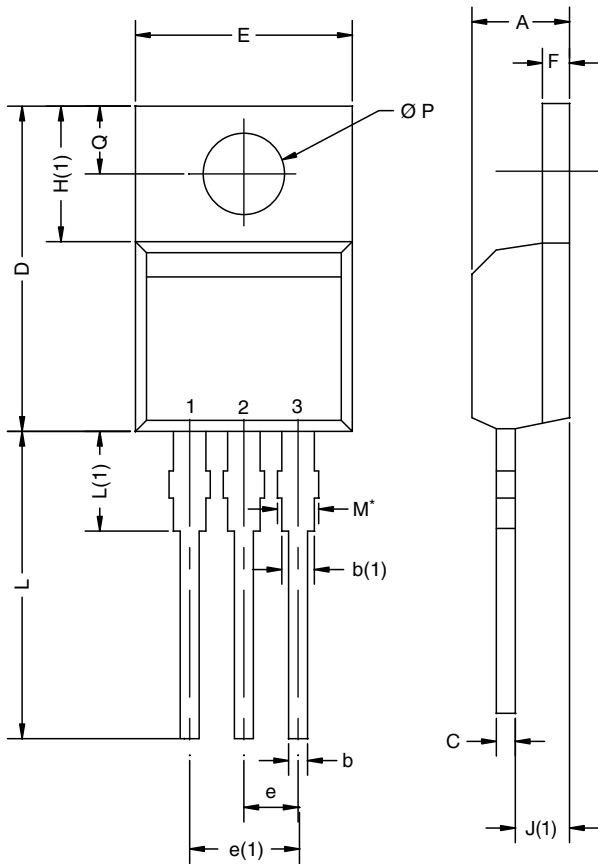
THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)


Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-220AB

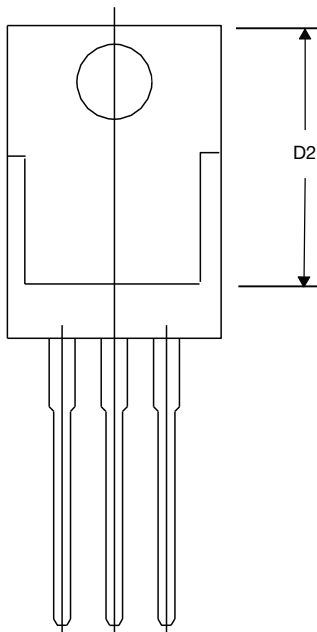


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: T14-0413-Rev. P, 16-Jun-14
DWG: 5471

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM



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